



PNP Power Amplifier Silicon Transistor

Qualified per MIL-PRF-19500/580

Qualified Levels:
JAN, JANTX and
JANTXV

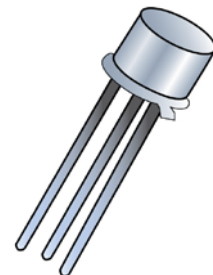
DESCRIPTION

This family of 2N4234, 2N4235, and 2N4236 silicon transistors are military qualified up to the JANTXV level for high-reliability applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N4234 and 2N4236 number
- JAN, JANTX, and JANTXV qualifications available per MIL-PRF-19500/580
- RoHS compliant version available



TO-205AD
(formerly TO-39)
Package

APPLICATIONS / BENEFITS

- Short leaded TO-205AD package
- Lightweight package
- Military and other high-reliability applications

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Parameters / Test Conditions	Symbol	Value	Unit
Junction & Storage Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	29	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	175	$^\circ\text{C/W}$
Total Power Dissipation ⁽¹⁾ @ $T_A = 25^\circ\text{C}$ ⁽¹⁾ @ $T_C = 25^\circ\text{C}$ ⁽²⁾	P_T	1.0 6.0	W
Collector – Emitter Voltage 2N4234 2N4235 2N4236	V_{CEO}	-40 -60 -80	V
Collector – Base Voltage 2N4234 2N4235 2N4236	V_{CBO}	-40 -60 -80	V
Emitter - Base Voltage	V_{EBO}	-7.0	V
Base Current	I_B	-0.5	A
Collector Current	I_C	-1.0	A

Notes: 1. Derated linearly by 5.7 mW/ $^\circ\text{C}$ for $T_A > +25^\circ\text{C}$
2. Derated linearly by 34 mW/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

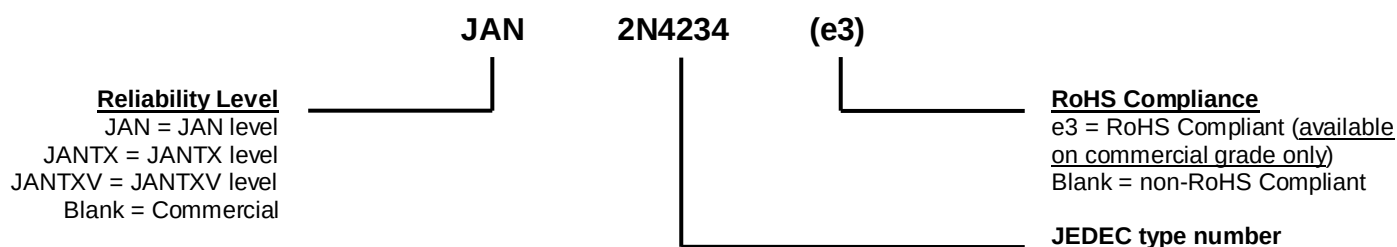
Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed, steel base, nickel cap
- TERMINALS: Steel Leads, nickel plated, then solder dipped or RoHS compliant matte-tin available on commercial grade only
- MARKING: Part number, date code, manufacturer's ID and serial number
- POLARITY: PNP
- WEIGHT: Approximately 1.064 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
I_B	Base current: The value of the dc current into the base terminal.
I_C	Collector current: The value of the dc current into the collector terminal.
I_E	Emitter current: The value of the dc current into the emitter terminal.
T_C	Case temperature: The temperature measured at a specified location on the case of a device.
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.
V_{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
V_{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.
V_{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.
V_{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
V_{EB}	Emitter-base voltage: The dc voltage between the emitter and the base
V_{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$, unless otherwise noted

Characteristics	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = -100\text{ mA}$	2N4234 2N4235 2N4236	$V_{(BR)CEO}$	-40 -60 -80	V
Collector-Emitter Cutoff Current $V_{CB} = -30\text{ V}$ $V_{CB} = -40\text{ V}$ $V_{CB} = -60\text{ V}$	2N4234 2N4235 2N4236	I_{CEO}	 -1.0 -1.0 -1.0	mA
Collector-Emitter Cutoff Current $V_{CB} = -40\text{ V}, V_{BE} = -1.5\text{ V}$ $V_{CB} = -60\text{ V}, V_{BE} = -1.5\text{ V}$ $V_{CB} = -80\text{ V}, V_{BE} = -1.5\text{ V}$	2N4234 2N4235 2N4236	I_{CEX}	 -100 -100 -100	nA
Collector-Base Cutoff Current $V_{CB} = -40\text{ V}$ $V_{CB} = -60\text{ V}$ $V_{CB} = -80\text{ V}$	2N4234 2N4235 2N4236	I_{CBO}	 -100 -100 -100	nA
Emitter-Base Cutoff Current $V_{BE} = -7.0\text{ V}$		I_{EBO}	-0.5	mA

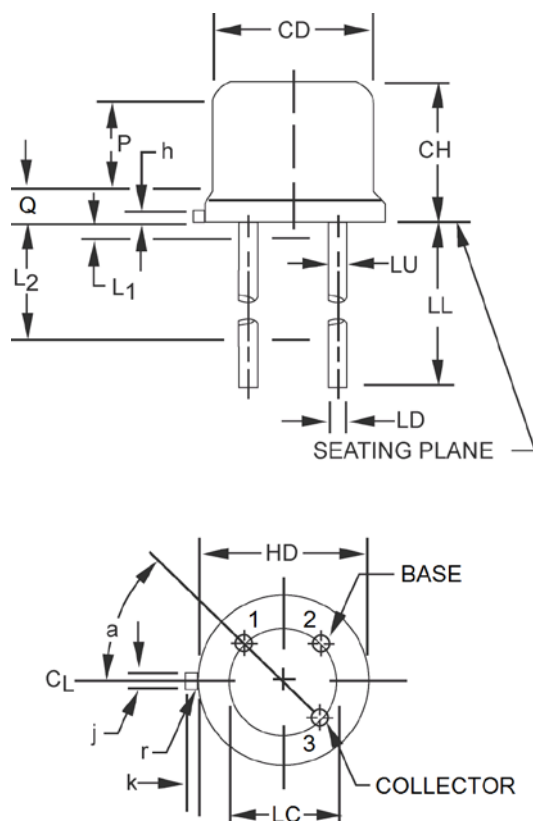
ON CHARACTERISTICS ⁽³⁾

Forward-Current Transfer Ratio $I_C = -100\text{ mA}, V_{CE} = -1.0\text{ V}$ $I_C = -250\text{ mA}, V_{CE} = -1.0\text{ V}$ $I_C = -500\text{ mA}, V_{CE} = -1.0\text{ V}$	h_{FE}	40 30 20	150	
Collector-Emitter Saturation Voltage $I_C = -1.0\text{ A}, I_B = -100\text{ mA}$ $I_C = -500\text{ mA}, I_B = -50\text{ mA}$	$V_{CE(sat)}$		-0.6 -0.4	V
Base-Emitter Saturation Voltage $I_C = -500\text{ mA}, I_B = -50\text{ mA}$ $I_C = -1.0\text{ A}, I_B = -100\text{ mA}$	$V_{BE(sat)}$		-1.1 -1.5	V

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -100\text{ mA}, V_{CE} = -10\text{ V}, f = 1\text{ MHz}$	$ h_{FE} $	3.0		
Output Capacitance $V_{CB} = -10\text{ V}, I_E = 0, f = 100\text{ MHz}$	C_{obo}		100	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted (continued)**SAFE OPERATING AREA****DC Tests** $T_C = +25\text{ }^{\circ}\text{C}$, 1 cycle, $t \geq 0.5\text{ s}$ **Test 1** $V_{CE} = -6.0\text{ V}$, $I_C = -1.0\text{ A}$ **Test 2** $V_{CE} = -12\text{ V}$, $I_C = -500\text{ mA}$ **Test 3** $V_{CE} = -30\text{ V}$, $I_C = -166\text{ mA}$ (2N4234) $V_{CE} = -50\text{ V}$, $I_C = -100\text{ mA}$ (2N4235) $V_{CE} = -70\text{ V}$, $I_C = -71\text{ mA}$ (2N4236)(3) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$

PACKAGE DIMENSIONS


Ltr	Dimensions				Notes
	Inch		Millimeters		
	Min	Max	Min	Max	
CD	0.305	0.335	7.75	8.51	
CH	0.240	0.260	6.10	6.60	
HD	0.335	0.370	8.51	9.40	
h	0.009	0.041	0.23	1.04	
j	0.028	0.034	0.71	0.86	3
k	0.029	0.045	0.74	1.14	3, 4
LD	0.016	0.021	0.41	0.53	8, 9
LL	0.500	0.750	12.7	19.05	
LC	0.200 TP		5.08 TP		7
LU	0.016	0.019	0.41	0.48	8, 9
L1	-	0.050	-	1.27	8, 9
L2	0.250	-	6.35	-	8, 9
P	0.100	-	2.54	-	7
Q	-	0.050	-	1.27	5
r	-	0.010	-	0.25	10
α	45° TP		45° TP		7

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. Beyond r (radius) maximum, TL shall be held for a minimum length of 0.011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
7. Leads at gauge plane 0.054 +0.001 -0.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within 0.007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
8. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
9. All three leads.
10. The collector shall be internally connected to the case.
11. Dimension r (radius) applies to both inside corners of tab.
12. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.